

IN THE ABSTRACT:

Please amend the Abstract originally appearing on page 18 of the application as follows:

ABSTRACT OF THE DISCLOSURE

A method, structure and system for forming a through-hole conductor in a semiconductor substrate includes forming a hole having an inner surface from a first side of the semiconductor substrate to a second side of the semiconductor substrate and plating the inner surface of the semiconductor substrate to form a conductive element when a plating solution is forced from the first side of the semiconductor substrate to the second side of the semiconductor substrate through the hole. The hole is plated in a generally planar plating topology from the first side to the second side of the semiconductor ~~wafer~~ substrate. The through-hole conductor may be formed in a plating system where the semiconductor substrate forms at least a partial partition between a higher pressure bath and a lower pressure bath with the plating solution passing through the hole causing plating within the inner surface of the hole.